2SK2116, 2SK2117

Silicon N-Channel MOS FET

HITACHI

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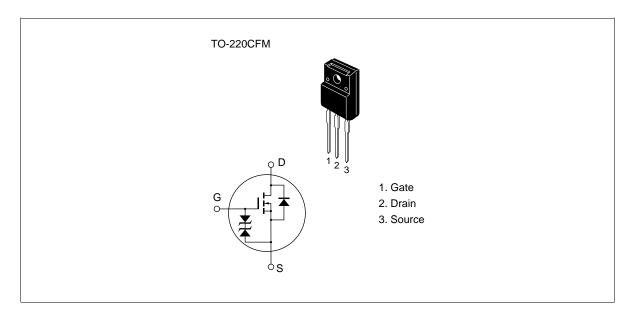
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for Switching regulator

Outline





2SK2116, 2SK2117

Ordering Information

| Type No. | V _{DSS} |
|----------|------------------|
| 2SK2116 | 450 V |
| 2SK2117 | 500 V |

Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

| Item | | Symbol | Ratings | Unit |
|---|---------|--------------------------|-------------|------|
| Drain to source voltage | 2SK2116 | V _{DSS} | 450 | V |
| | 2SK2117 | V_{DSS} | 500 | |
| Gate to source voltage | | $V_{\sf GSS}$ | ±30 | V |
| Drain current | | I _D | 7 | А |
| Drain peak current | | l _{D(pulse)} *1 | 28 | A |
| Body to drain diode reverse drain current | | I _{DR} | 7 | A |
| Channel dissipation | | Pch*2 | 35 | W |
| Channel temperature | | Tch | 150 | °C |
| Storage temperature | | Tstg | -55 to +150 | °C |

Notes 1. PW 10 µs, duty cycle 1 %

2. Value at Tc = 25 °C

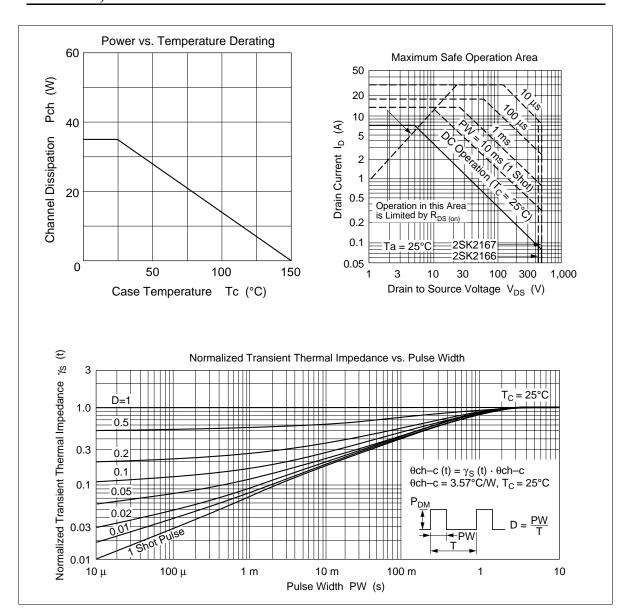
Electrical Characteristics ($Ta = 25^{\circ}C$)

| Item | | Symbol | Min | Тур | Max | Unit | Test conditions |
|---------------------------------|---------------|---------------------------------|-----|------|-----|------|--|
| Drain to source | 2SK2116 | $V_{(BR)DSS}$ | 450 | _ | _ | V | $I_D = 10 \text{ mA}, V_{GS} = 0$ |
| breakdown voltage | 2SK2117 | _ | 500 | | | | |
| Gate to source b voltage | reakdown | $V_{(BR)GSS}$ | ±30 | _ | _ | V | $I_{G} = \pm 100 \ \mu A, \ V_{DS} = 0$ |
| Gate to source le | eak current | I _{GSS} | _ | _ | ±10 | μΑ | $V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$ |
| Zero gate | 2SK2116 | I _{DSS} | _ | _ | 250 | μA | $V_{DS} = 360 \text{ V}, V_{GS} = 0$ |
| voltage drain current | 2SK2117 | | | | | | $V_{DS} = 400 \text{ V}, V_{GS} = 0$ |
| Gate to source co | utoff voltage | $V_{\rm GS(off)}$ | 2.0 | _ | 3.0 | V | $I_{D} = 1 \text{ mA}, V_{DS} = 10 \text{ V}$ |
| Static drain to | 2SK2116 | $R_{\scriptscriptstyle DS(on)}$ | _ | 0.6 | 8.0 | | $I_D = 4 \text{ A}, V_{GS} = 10 \text{ V}^{*1}$ |
| source on state resistance | 2SK2117 | | _ | 0.7 | 0.9 | | |
| Forward transfer | admittance | $ y_{fs} $ | 4.0 | 6.5 | _ | S | $I_D = 4 A$ $V_{DS} = 10 V^{*1}$ |
| Input capacitance | е | Ciss | _ | 1050 | _ | pF | V _{DS} = 10 V |
| Output capacitan | ice | Coss | _ | 280 | _ | pF | $V_{GS} = 0$ |
| Reverse transfer | capacitance | Crss | _ | 40 | _ | pF | f = 1 MHz |
| Turn-on delay tin | ne | $\mathbf{t}_{\text{d(on)}}$ | _ | 15 | _ | ns | $I_D = 4 A$ |
| Rise time | | t _r | _ | 55 | _ | ns | V _{GS} = 10 V |
| Turn-off delay tim | ne | $t_{\text{d(off)}}$ | _ | 95 | _ | ns | $R_{L} = 7.5$ |
| Fall time | | t_{f} | _ | 40 | _ | ns | |
| Body to drain dio voltage | de forward | V_{DF} | _ | 0.95 | _ | V | $I_F = 7 \text{ A}, V_{GS} = 0$ |
| Body to drain dio recovery time | de reverse | t _{rr} | _ | 320 | _ | ns | $I_F = 7 \text{ A}, V_{GS} = 0,$ diF / dt = 100 A / μ s |

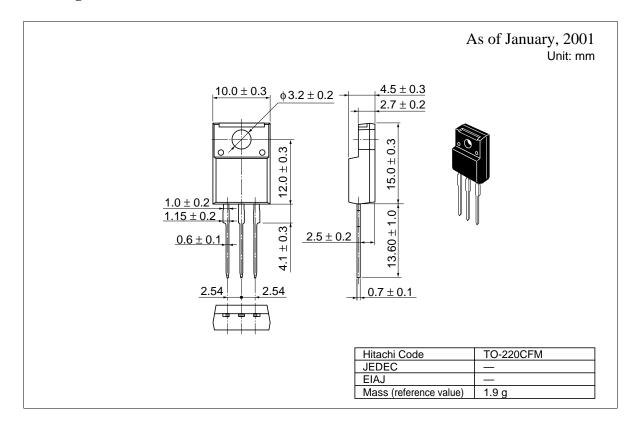
Note 1. Pulse Test

See characteristic curve of 2SK1157, 2SK1158.

2SK2116, 2SK2117



Package Dimensions



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